Silicon NPN Power Transistors 2SC2774

DESCRIPTION

·With MT-200 package
·High power dissipation
·High current capability

APPLICATIONS

·For audio power amplifier and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

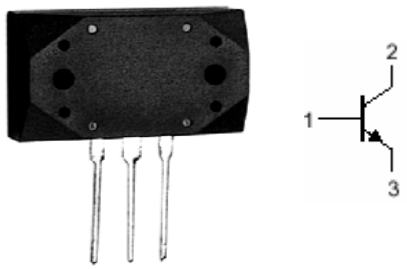

Fig.1 simplified outline (MT-200) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		17	A
I_B	Base current		5	A
P_C	Collector power dissipation	T_C=25□	200	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

Silicon NPN Power Transistors 2SC2774

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=25mA ; I_B=0	200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ; I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=5A; I_B=0.5A			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=200V; I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			100	μA
h_{FE}	DC current gain	I_C=5A ; V_{CE}=4V	50		140	
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=10V;f=1MHz		300		pF
f_T	Transition frequency	I_C=2A ; V_{CE}=12V		20		MHz

◆ **h_{FE} classifications**

O	Y
50-100	70-140

PACKAGE OUTLINE

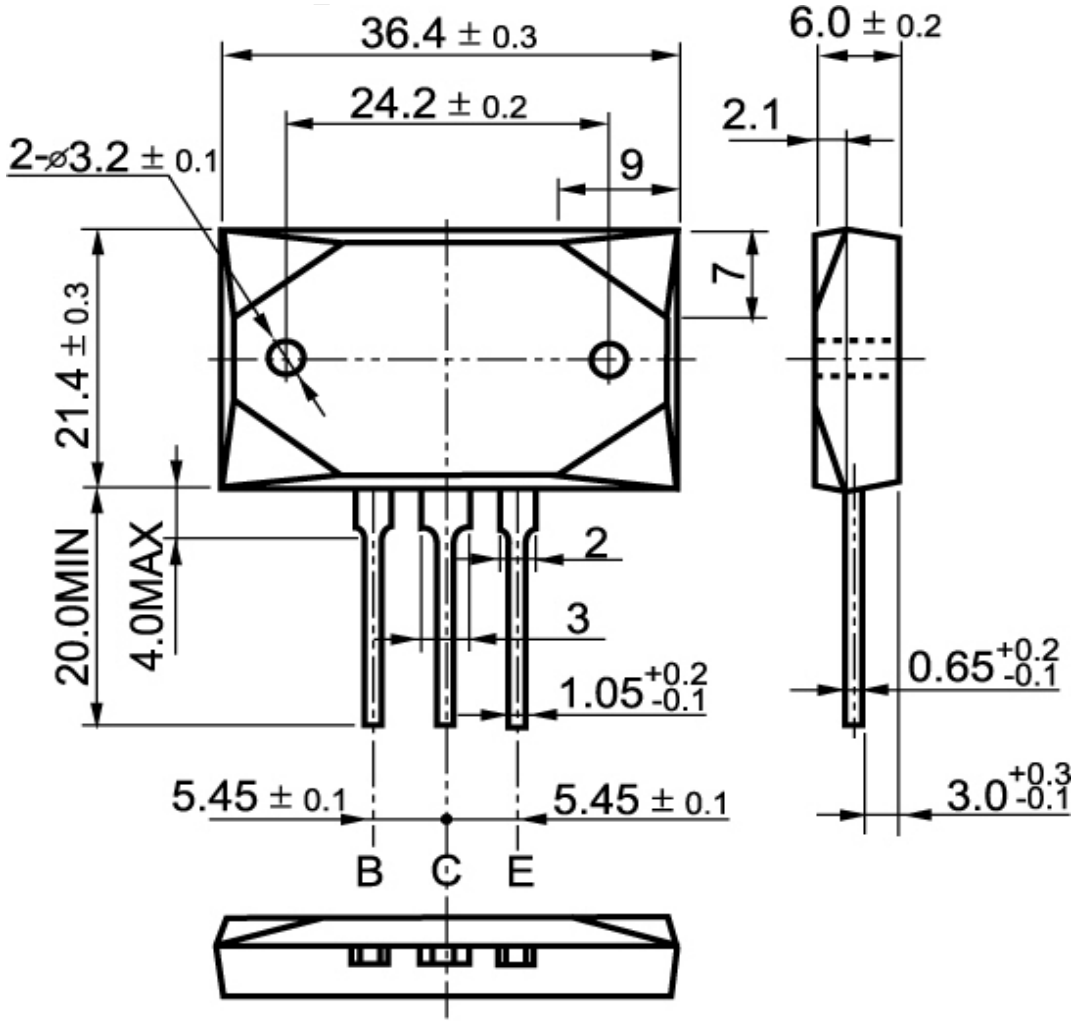

Fig.2 outline dimensions